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THIN FILM SEMICONDUCTOR DEVICE, PROCESS FOR
FABRICATING THE SAME, AND SILICON FILM

Abstract of the Disclosure

There is Disclosed a semiconductor device comprising a silicon film formed on a substrate having at least a surface formed of an insulative material, the silicon film being heat-treated at a temperature below 600 °C and being partially coated with a silicon oxide film formed by electronic cyclotron resonance plasma CVD.

THIS SHEET HAS BEEN
REPLACED